Yasuyuki Miyamoto

List of Publications by Year
in descending order

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168	2,732	471509	206112
papers	citations	17 h-index	48 g-index

171	171	171	1625
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Simulation Study of Gate-Drain Leakage Current and Density of Polarization Charge at Heterojunction Interface in GaN HEMTs. IEEJ Transactions on Electronics, Information and Systems, 2022, 142, 348-353.	0.2	1
2	Wet etching for isolation of N-polar GaN HEMT structure by electrodeless photo-assisted electrochemical reaction. Japanese Journal of Applied Physics, 2021, 60, SCCF06.	1.5	1
3	Circuit speed oriented device design scheme for GaAsSb/InGaAs double-gate hetero-junction tunnel FETs. Japanese Journal of Applied Physics, 2020, 59, SGGA06.	1.5	2
4	Fabrication of Si photonic waveguides by electron beam lithography using improved proximity effect correction. Japanese Journal of Applied Physics, 2020, 59, 126502.	1.5	12
5	N-polar GaN HEMT with Al2O3gate insulator. , 2019, , .		0
6	Effect of increasing gate capacitance on the performance of a p-MoS₂/HfS₂ van der Waals heterostructure tunneling field-effect transistor. Japanese Journal of Applied Physics, 2019, 58, SBBH02.	1.5	9
7	Performance improvement of a p-MoS₂/HfS₂ van der Waals heterostructure tunneling FET by UV-O₃ treatment. Applied Physics Express, 2019, 12, 065005.	2.4	9
8	Regrown source/drain in InGaAs multi-gate MOSFETs. Journal of Crystal Growth, 2019, 522, 11-15.	1.5	3
9	Annealing temperature dependence of alloy contact for N-polar GaN HEMT structure. Japanese Journal of Applied Physics, 2019, 58, SCCD14.	1.5	7
10	GaAsSb/InGaAs double-gate vertical tunnel FET with a subthreshold slope of 56 mV dec^{âˆ’1} at room temperature. Japanese Journal of Applied Physics, 2019, 58, SBBA08.	1.5	3
11	A Method for Determining Trap Distributions of Specific Channel Surfaces in InGaAs Tri-Gate MOSFETs. IEEE Journal of the Electron Devices Society, 2018, 6, 408-412.	2.1	6
12	High Power, 14xx-nm Eye-safe, Epitaxially Stacked Pulse Laser for Detection and Ranging Applications. , 2018, , .		5
13	Type-II HfS₂/MoS₂ Heterojunction Transistors. IEICE Transactions on Electronics, 2018, E101.C, 338-342.	0.6	6
14	Performance Improvement of HfS2 Transistors by Atomic Layer Deposition of HfO2. IEEE Nanotechnology Magazine, 2017, 16, 582-587.	2.0	16
15	Vacuum Annealing and Passivation of HfS₂ FET for Mitigation of Atmospheric Degradation. IEICE Transactions on Electronics, 2017, E100.C, 453-457.	0.6	8
16	Operation of 16-nm InGaAs channel multi-gate MOSFETs with regrown source/drain. , 2016, , .		5
17	InAlGaN/GaN-HEMT device technologies for W-band high-power amplifier. , 2016, , .		4
18	Few-layer HfS2 transistors. Scientific Reports, 2016, 6, 22277.	3.3	131

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19	Fin width dependence on gate controllability of InGaAs channel FinFETs with regrown source/drain. Solid-State Electronics, 2016, 126, 92-95.	1.4	3
20	Experimental approach for feasibility of superlattice FETs. , 2016, , .		1
21	Recent progress in compound semiconductor electron devices. IEICE Electronics Express, 2016, 13, 20162002-20162002.	0.8	2
22	Scaling limit for InGaAs/GaAsSb heterojunction double-gate tunnel FETs from the viewpoint of direct band-to-band tunneling from source to drain induced off-characteristics deterioration. Japanese Journal of Applied Physics, 2016, 55, 070303.	1.5	3
23	Source and Drain Concentration Dependence on Double Gate GaAsSb/InGaAs Tunnel FET. IEEJ Transactions on Electronics, Information and Systems, 2016, 136, 467-473.	0.2	1
24	InGaAs/AlAs triple-barrier pâ€“iâ€“n junction diode for realizing superlattice-based FET for steep slope. Japanese Journal of Applied Physics, 2016, 55, 118004.	1.5	3
25	MOSFET with III-V Channel. IEEJ Transactions on Electronics, Information and Systems, 2016, 136, 437-443.	0.2	0
26	Permeability-controlled optical modulator with Tri-gate metamaterial: control of permeability on InP-based photonic integration platform. Scientific Reports, 2015, 5, 8985.	3.3	11
27	Collapse-free high power InAlGaN/GaN-HEMT with 3 W/mm at 96 GHz. , 2015, , .		51
28	Body width dependence of subthreshold slope and on-current in GaAsSb/InGaAs double-gate vertical tunnel FETs. Japanese Journal of Applied Physics, 2015, 54, 04DF10.	1.5	7
29	Potential of Enhancement Mode In_{0.65}Ga_{0.35}As/InAs/In_{0.65}Ga_{0.35}As HEMTs for Using in High-Speed and Low-Power Logic Applications. ECS Journal of Solid State Science and Technology, 2015, 4, N157-N159.	1.8	9
30	Loss reduction of Si optical waveguides by beam step-size fracturing technique in electron beam lithography. Japanese Journal of Applied Physics, 2014, 53, 06JB04.	1.5	1
31	InGaAs tri-gate MOSFETs with MOVPE regrown source/drain. , 2014, , .		6
32	Growth process for high performance of InGaAs MOSFETs. , 2014, , .		0
33	InGaAs MOSFET source structures toward high speed/low power applications. , 2014, , .		1
34	Channel thickness dependence on InGaAs MOSFET with n-InP source for high current density. IEICE Electronics Express, 2014, 11, 20140567-20140567.	0.8	2
35	Delay Time Component of InGaAs MOSFET Caused by Dynamic Source Resistance. IEICE Transactions on Electronics, 2014, E97.C, 419-422.	0.6	0
36	Sub-50-nm InGaAs MOSFET with n-InP source on Si substrate. , 2013, , .		7

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37	Performance Evaluation of InGaSb/AlSb P-Channel High-Hole-Mobility Transistor Faricated Using BCl3Dry Etching. Japanese Journal of Applied Physics, 2013, 52, 020203.	1.5	2
38	InAs Thin-Channel High-Electron-Mobility Transistors with Very High Current-Gain Cutoff Frequency for Emerging Submillimeter-Wave Applications. Applied Physics Express, 2013, 6, 034001.	2.4	94
39	Metal-Insulator-Semiconductor Field-Effect Transistors. Active and Passive Electronic Components, 2013, 2013, 1-2.	0.3	0
40	High electron mobility triangular InGaAs-OI nMOSFETs with (111)B side surfaces formed by MOVPE growth on narrow fin structures. , 2013, , .		7
41	High Open-Circuit Voltage Gain in Vertical InGaAs Channel Metalâ€“Insulatorâ€“Semiconductor Field-Effect Transistor Using Heavily Doped Drain Region and Narrow Channel Mesa. Japanese Journal of Applied Physics, 2013, 52, 04CF05.	1.5	1
42	Reduction of Base-Collector Capacitance in InP/InGaAs DHBT with Buried SiO₂ Wires. IEICE Transactions on Electronics, 2012, E95.C, 917-920.	0.6	0
43	Simulation Study and Reduction of Reverse Gate Leakage Current for GaN HEMTs. , 2012, , .		1
44	71 mV/dec of sub-threshold slope in vertical tunnel field-effect transistors with GaAsSb/InGaAs heterostructure. , 2012, , .		10
45	InP HBT with 55-nm-wide emitter and relationship between emitter width and current density. , 2012, , .		2
46	Bias-Dependent Radio Frequency Performance for 40 nm InAs High-Electron-Mobility Transistor with a Cutoff Frequency Higher than 600 GHz. Japanese Journal of Applied Physics, 2012, 51, 110203.	1.5	5
47	Reduction of Output Conductance in Vertical InGaAs Channel Metalâ€“Insulatorâ€“Semiconductor Field-Effect Transistor Using Heavily Doped Drain Region. Applied Physics Express, 2012, 5, 024101.	2.4	1
48	Fabrication of InP/InGaAs SHBT on Si Substrate by Using Transferred Substrate Process. IEICE Transactions on Electronics, 2012, E95.C, 1323-1326.	0.6	1
49	Reduction of Access Resistance of InP/InGaAs Composite-Channel MOSFET with Back-Source Electrode. IEICE Transactions on Electronics, 2012, E95.C, 904-909.	0.6	1
50	High drain current (>2A/mm) InGaAs channel MOSFET at V<inf>D</inf>=0.5V with shrinkage of channel length by InP anisotropic etching. , 2011, , .		30
51	Deviation From Proportional Relationship Between Emitter Charging Time and Inverse Current of Heterojunction Bipolar Transistors Operating at High Current Density. IEEE Electron Device Letters, 2011, 32, 491-493.	3.9	3
52	High-current-density InP ultrafine devices for high-speed operation. , 2011, , .		0
53	Flip-Chip Packaging of Low-Noise Metamorphic High Electron Mobility Transistors on Low-Cost Organic Substrate. Japanese Journal of Applied Physics, 2011, 50, 096503.	1.5	1
54	InP/InGaAs Composite Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors with Regrown Source and Al₂O₃Gate Dielectric Exhibiting Maximum Drain Current Exceeding 1.3 mA/Âµm. Applied Physics Express, 2011, 4, 054201.	2.4	35

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55	Vertical InGaAs Channel Metalâ€“Insulatorâ€“Semiconductor Field Effect Transistor with High Current Density. Japanese Journal of Applied Physics, 2011, 50, 014102.	1.5	4
56	Flip-Chip Packaging of Low-Noise Metamorphic High Electron Mobility Transistors on Low-Cost Organic Substrate. Japanese Journal of Applied Physics, 2011, 50, 096503.	1.5	1
57	Vertical InGaAs Channel Metalâ€“Insulatorâ€“Semiconductor Field Effect Transistor with High Current Density. Japanese Journal of Applied Physics, 2011, 50, 014102.	1.5	4
58	Fabrication of InP/InGaAs DHBTs with Buried SiO2 Wires. IEICE Transactions on Electronics, 2011, E94-C, 830-834.	0.6	1
59	Submicron InP/InGaAs Composite-Channel Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor with Selectively Regrown n⁺-Source. Applied Physics Express, 2010, 3, 094201.	2.4	17
60	Fabrication of Vertical InGaAs Channel Metalâ€“Insulatorâ€“Semiconductor Field Effect Transistor with a 15-nm-Wide Mesa Structure and a Drain Current Density of 7 MA/cm2. Applied Physics Express, 2010, 3, 084101.	2.4	14
61	Monte Carlo Analysis of Base Transit Times of InP/GaInAs Heterojunction Bipolar Transistors with Ultrathin Graded Bases. Japanese Journal of Applied Physics, 2010, 49, 024302.	1.5	3
62	Submicron InP/InGaAs composite channel MOSFETs with selectively regrown N⁺-source/drain buried in channel undercut. , 2010, , .		2
63	Selective undercut etching for ultra narrow mesa structure in vertical InGaAs channel MISFET. , 2010, , .		0
64	Bonding temperature effect on the performance of flip chip assembled 150nm mHEMT device on organic substrate. , 2010, , .		0
65	Submicron-channel InGaAs MISFET with epitaxially grown source. , 2010, , .		0
66	30-GHz Low-Noise Performance of 100-nm-Gate-Recessed n-GaN/AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2010, 31, 105-107.	3.9	21
67	RF Performance Improvement of Metamorphic High-Electron Mobility Transistor Using $(hbox{In}_{x}hbox{Ga}_{1 - x}hbox{As})_{m}/(hbox{InAs})_{n}$ Superlattice-Channel Structure for Millimeter-Wave Applications. IEEE Electron Device Letters, 2010, 31, 677-679.	3.9	3
68	An 80 nm In<inf>0.7</inf>Ga<inf>0.3</inf>As MHEMT with flip-chip packaging for W-band low noise applications. , 2010, , .		0
69	Estimation of Collector Current Spreading in InGaAs SHBT Having 75-nm-Thick Collector. IEICE Transactions on Electronics, 2010, E93-C, 644-647.	0.6	2
70	InP/InGaAs MOSFET with Back-Electrode Structure Bonded on Si Substrate Using a BCB Adhesive Layer. , 2010, , .		1
71	A novel metamorphic high electron mobility transistors with (In<inf>x</inf>Ga<inf>1-x</inf>As)<inf>m</inf>/(InAs)<inf>n</inf> superlattice channel layer for millimeter-wave applications. , 2009, , .		0
72	InAs-Channel Metal-Oxide-Semiconductor HEMTs with Atomic-Layer-Deposited Al[sub 2]O[sub 3] Gate Dielectric. Electrochemical and Solid-State Letters, 2009, 12, H456.	2.2	1

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73	InAs-Channel High-Electron-Mobility Transistors for Ultralow-Power Low Noise Amplifier Applications. Japanese Journal of Applied Physics, 2009, 48, 04C094.	1.5	1
74	A 40-nm-Gate InAs/In<inf>0.7</inf>Ga<inf>0.3</inf>As Composite-Channel HEMT with 2200 mS/mm and 500-GHz f<inf>T</inf>. , 2009, , .		0
75	Fabrication of InP/InGaAs channel MOSFET with MOVPE selectively regrown source. , 2009, , .		0
76	Vertical InGaAs-MOSFET with hetero-launcher and undoped channel. , 2009, , .		1
77	Cutoff frequency characteristics of gate-controlled hot-electron transistors by Monte Carlo simulation. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 70-73.	0.8	9
78	Investigation of impact ionization from InxGa1-xAs to InAs Channel HEMTs for high speed and low power applications. , 2008, , .		0
79	Hot electron transistors controlled by insulated gate with 70 NM-wide emitter. , 2008, , .		0
80	Increment of voltage gain of InP/InGaAs hot electron transistors controlled by insulated gate. , 2008, , .		0
81	RF and Logic Performance Improvement of $ hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}/hbox{InAs}/hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}$ Composite-Channel HEMT Using Gate-Sinking Technology. IEEE Electron Device Letters, 2008, 29, 290-293.	3.9	26
82	InAs High Electron Mobility Transistors with Buried Gate for Ultralow-Power-Consumption Low-Noise Amplifier Application. Japanese Journal of Applied Physics, 2008, 47, 7119-7121.	1.5	12
83	InP/InGaAs Hot Electron Transistors with Insulated Gate. Japanese Journal of Applied Physics, 2007, 46, L617-L619.	1.5	7
84	Increase in Collector Current in Hot-Electron Transistors Controlled by Gate Bias. Japanese Journal of Applied Physics, 2007, 46, L202-L204.	1.5	7
85	High Performance InAs-Channel HEMT for Low Voltage Milimeter Wave Applications. , 2007, , .		0
86	High-Performance In0.52Al0.48As/In0.6Ga0.4As Power Metamorphic High Electron Mobility Transistor for Ka-Band Applications. Japanese Journal of Applied Physics, 2007, 46, 3385-3387.	1.5	1
87	Investigation of Impact Ionization in InAs-Channel HEMT for High-Speed and Low-Power Applications. IEEE Electron Device Letters, 2007, 28, 856-858.	3.9	39
88	Emitter layer design for high-speed InP HBTs with high reliability. , 2007, , .		5
89	InP buried growth of SiO2 wires toward reduction of collector capacitance in HBT. Journal of Crystal Growth, 2007, 298, 867-870.	1.5	3
90	MC simulation of ultrafast transistor using ballistic electron in intrinsic semiconductor and its fabrication feasibility. Journal of Physics: Conference Series, 2006, 38, 208-211.	0.4	4

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91	Charging Time of Double-Layer Emitter in Heterojunction Bipolar Transistor Based on Transmission Formalism. Japanese Journal of Applied Physics, 2006, 45, L935-L937.	1.5	5
92	High-Performance In_{0.52}Al_{0.48}As/In_{0.6}Ga_{0.4}As Power Metamorphic HEMT for Ka-Band Applications. , 2006, , .		0
93	Current Gain and Voltage Gain in Hot Electron Transistors without Base Layer. IEICE Transactions on Electronics, 2006, E89-C, 972-978.	0.6	6
94	Impact of Latent Image Quality on Line Edge Roughness in Electron Beam Lithography. Japanese Journal of Applied Physics, 2004, 43, 3739-3743.	1.5	8
95	InP Hot Electron Transistors with Emitter Mesa Fabricated between Gate Electrodes for Reduction in Emitter-Gate Gate-Leakage Current. Japanese Journal of Applied Physics, 2004, 43, L183-L186.	1.5	1
96	Challenges to Ultra-thin Resist Process for LEEPL. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2004, 17, 581-586.	0.3	2
97	Youngâ€™s Double-Slit Interference Observation of Hot Electrons in Semiconductors. Physical Review Letters, 2003, 91, 216803.	7.8	9
98	InP Hot Electron Transistors with a Buried Metal Gate. Japanese Journal of Applied Physics, 2003, 42, 7221-7226.	1.5	21
99	Fabrication of InP/GaInAs Double Heterojunction Bipolar Transistors with a 0.1-Âµm-Wide Emitter. Japanese Journal of Applied Physics, 2002, 41, L121-L123.	1.5	3
100	Reduction of Base-Collector Capacitance in Submicron InP/GaInAs Heterojunction Bipolar Transistors with Buried Tungsten Wires. Japanese Journal of Applied Physics, 2001, 40, L735-L737.	1.5	5
101	Toward nano-metal buried structure in InP â€“ 20 nm wire and InP buried growth of tungsten. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 896-901.	2.7	5
102	Fabrication and transport properties of 50-nm-wide Au/Cr/GaInAs electrode for electron wave interference device. Applied Surface Science, 2000, 159-160, 179-185.	6.1	11
103	First Fabrication of GaInAs/InP Buried Metal Heterojunction Bipolar Transistor and Reduction of Base-Collector Capacitance. Japanese Journal of Applied Physics, 2000, 39, L503-L505.	1.5	3
104	Barrier thickness dependence of peak current density in GaInAs/AlAs/InP resonant tunneling diodes by MOVPE. Solid-State Electronics, 1999, 43, 1395-1398.	1.4	15
105	Sub-micron GaInAs/InP hot electron transistors by EBL process and size dependence of current gain. Solid-State Electronics, 1998, 42, 1467-1470.	1.4	2
106	25 nm pitch GaInAs/InP buried structure: Improvement by calixarene as an electron beam resist and tertiarybutylphosphine as a P source in organometallic vapor phase epitaxy regrowth. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 3894.	1.6	5
107	Improvement of GMR characteristics in [Ni/sub 81/Fe/sub 19//Cu] multilayers by interfacial modulation technique using Kr ions. IEEE Transactions on Magnetics, 1998, 34, 921-923.	2.1	1
108	Effect of Spacer Layer Thickness on Energy Level Width Narrowing in GaInAs/InP Resonant Tunneling Diodes Grown by Organo-Metallic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1998, 37, 445-449.	1.5	10

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109	A 40-nm-pitch double-slit experiment of hot electrons in a semiconductor under a magnetic field. Applied Physics Letters, 1997, 70, 93-95.	3.3	17
110	Influence of a finite energy width on the hot electron double-slit interference experiment: A design of the emitter structure. Journal of Applied Physics, 1997, 82, 3846-3852.	2.5	6
111	High Peak-to-Valley Current Ratio GaInAs/GaInP Resonant Tunneling Diodes. Japanese Journal of Applied Physics, 1997, 36, 5079-5080.	1.5	3
112	Characterization of GaInAs/InP Triple-Barrier Resonant Tunneling Diodes Grown by Organo-Metallic Vapor Phase Epitaxy for High-Temperature Estimation of Phase Coherent Length of Electrons. Japanese Journal of Applied Physics, 1997, 36, 1846-1848.	1.5	10
113	MIS emitter with epitaxial CaF₂ layer as insulator. , 1997, , .		0
114	Atomically flat OMVPE growth of GaInAs and InP observed by AFM for level narrowing in resonant tunneling diodes. Journal of Crystal Growth, 1997, 179, 18-25.	1.5	12
115	A self-consistent method for complete small-signal parameter extraction of InP-based heterojunction bipolar transistors (HBT's). IEEE Transactions on Microwave Theory and Techniques, 1997, 45, 39-45.	4.6	39
116	Hot electron interference by 40 nm-pitch double slit buried in semiconductor. Microelectronic Engineering, 1997, 35, 337-340.	2.4	0
117	Electrical properties of 100 nm pitch CrAu fine electrodes with 40 nm width on GaInAs toward hot electron interference/diffraction devices. Microelectronic Engineering, 1997, 35, 241-244.	2.4	0
118	Effects of Ni/sub 81/Fe/sub 19/ underlayer and Ar ion bombardment to deposition of (111) oriented Fe/sub 50/Mn/sub 50/ layers for spin valve devices. IEEE Transactions on Magnetics, 1996, 32, 4672-4674.	2.1	3
119	Reduction of base-collector capacitance by undercutting the collector and subcollector in GaInAs/InP DHBTs. IEEE Electron Device Letters, 1996, 17, 97-99.	3.9	27
120	Detection of hot electron current with scanning hot electron microscopy. Applied Physics Letters, 1996, 69, 2196-2198.	3.3	14
121	Investigations of GMR characteristics and crystal structures for Ni/sub 81/Fe/sub 19//Cu multilayers with Ar ion bombardment on interfaces. IEEE Transactions on Magnetics, 1996, 32, 4719-4721.	2.1	10
122	Seventy-nm-Pitch Patterning on CaF2by e-beam Exposure. Japanese Journal of Applied Physics, 1996, 35, 6342-6343.	1.5	3
123	Effect of ion bombardment and bias fielding for [Ni/sub 81/Fe/sub 19//Cu] multilayers with giant magnetoresistance deposited by dual ion beam sputtering. IEEE Transactions on Magnetics, 1995, 31, 4103-4105.	2.1	3
124	GaInAs/InP DHBT incorporating thick extrinsic base and selectively regrown emitter. Electronics Letters, 1995, 31, 1510-1511.	1.0	4
125	Nanostructure Alignment for Hot Electron Interference/Diffraction Devices. Japanese Journal of Applied Physics, 1995, 34, 4436-4438.	1.5	7
126	Ultrafine Fabrication Technique for Hot Electron Interference/Diffraction Devices. Japanese Journal of Applied Physics, 1994, 33, 925-928.	1.5	18

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127	Estimation of Phase Coherent Length of Hot Electrons in GaInAs Using Resonant Tunneling Diodes. Japanese Journal of Applied Physics, 1994, 33, 6491-6495.	1.5	10
128	GaInAs/InP organometallic vapor phase epitaxy regrowth for ultrafine buried heterostructures with 50 nm pitch toward electron wave devices. Journal of Crystal Growth, 1994, 145, 698-701.	1.5	3
129	Observation of InP and GaInAs Surfaces after (NH4)2Sx Treatment by a Scanning Tunneling Microscope. , 1994, , 513-517.		0
130	Room-temperature operation of GaInAs/GaInAsP/InP SCH lasers with quantum-wire size active region. IEEE Journal of Quantum Electronics, 1993, 29, 2123-2133.	1.9	30
131	Influence of Impurities on the Performance of Doped-Well GaInAs/InP Resonant Tunneling Diodes. Japanese Journal of Applied Physics, 1993, 32, L243-L246.	1.5	8
132	Observation of InP Surfaces after (NH4)2SxTreatment by a Scanning Tunneling Microscope. Japanese Journal of Applied Physics, 1993, 32, L444-L446.	1.5	4
133	Threshold current reduction of GaInAs/GaInAsP/InP SCH quantum-well lasers with wire-like active region by using p-type substrates. IEEE Photonics Technology Letters, 1992, 4, 964-966.	2.5	6
134	High P/V ratio of GaInAs/InP resonant tunneling diode grown by OMVPE. Journal of Crystal Growth, 1992, 124, 807-811.	1.5	9
135	Room temperature operation of GaInAs-GaInAsP-InP SCH multiquantum-film laser with narrow wire-like active region. IEEE Photonics Technology Letters, 1991, 3, 191-192.	2.5	12
136	Improvement of Regrown Interface in InP Organo-Metallic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1991, 30, L672-L674.	1.5	13
137	Buried rectangular GaInAs/InP corrugations of 70 nm pitch fabricated by OMVPE. Electronics Letters, 1990, 26, 875.	1.0	10
138	OMVPE buried ultrafine periodic structures in GaInAs and InP. Microelectronic Engineering, 1990, 11, 93-96.	2.4	2
139	High current gain GaInAs/InP hot electron transistor. Electronics Letters, 1990, 26, 1055.	1.0	10
140	Negative differential conductance due to resonant states in GaInAs/InP hotâ€electron transistors. Applied Physics Letters, 1990, 57, 2104-2106.	3.3	5
141	High-Quality n-GaInAs Grown by OMVPE Using Si2H6by High-Velocity Flow. Japanese Journal of Applied Physics, 1990, 29, 1910-1911.	1.5	3
142	Observation of quantum coherence properties of the hot electron. IEEE Transactions on Electron Devices, 1989, 36, 2620.	3.0	1
143	Very fine corrugations formed on InP by wet chemical etching and electron beam lithography. Electronics Letters, 1989, 25, 238.	1.0	5
144	Wet Chemical Etching for Ultrafine Periodic Structure: Rectangular InP Corrugations of 70 nm Pitch and 100 nm Depth. Japanese Journal of Applied Physics, 1989, 28, 2193-2196.	1.5	27

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145	Threshold current density of GaInAsP/InP quantum-box lasers. IEEE Journal of Quantum Electronics, 1989, 25, 2001-2006.	1.9	102
146	High-efficiency hot-electron transport in GaInAs/InP hot electron transistor grown by OMVPE. Electronics Letters, 1989, 25, 704-705.	1.0	3
147	OMVPE conditions for GaInAs/InP heterointerfaces and superlattices. Journal of Crystal Growth, 1988, 93, 353-358.	1.5	9
148	Fabrication technique for GaInAsP/InP quantum wire structure by LP-MOVPE. Journal of Crystal Growth, 1988, 93, 365-369.	1.5	15
149	GaInAsP/InP single-quantum-well (SQW) laser with wire-like active region towards quantum wire laser. Electronics Letters, 1988, 24, 824.	1.0	18
150	GaInAs/InP Hot Electron Transistors Grown by OMVPE. Japanese Journal of Applied Physics, 1987, 26, L911-L913.	1.5	4
151	Light Emission from Quantum-Box Structure by Current Injection. Japanese Journal of Applied Physics, 1987, 26, L225-L227.	1.5	97
152	GaInAsP/InP Single Quantum-Well Lasers by OMVPE. Japanese Journal of Applied Physics, 1987, 26, L176-L178.	1.5	7
153	Gain and the threshold of three-dimensional quantum-box lasers. IEEE Journal of Quantum Electronics, 1986, 22, 1915-1921.	1.9	1,054
154	Theoretical Gain of Quantum-Well Wire Lasers. Japanese Journal of Applied Physics, 1985, 24, L95-L97.	1.5	187
155	Conditions for OMVPE Growth of GaInAsP/InP Crystal. Japanese Journal of Applied Physics, 1984, 23, 1182-1189.	1.5	35
156	Alloy composition and flow rates in GaxIn1â^'xAsyP1â^'y lattice-matched to InP grown by MO-CVD. Electronics Letters, 1983, 19, 1036.	1.0	12
157	C/sub BC/ reduction in GaInAs/InP buried metal heterojunction bipolar transistor. , 0, , .		2
158	High P/V Ratio of GaInAs/InP Resonant Tunneling Diode by OMVPE. , 0, , .		0
159	GMR Characteristics of Ni/sub 81/Fe/sub 19/ Cu Multilayers Deposited by Kr Sputtering with Ar Ion Bombardment on Interfaces. , 0, , .		0
160	Analysis of deflection sub-millimeter-wave amplifier. , 0, , .		0
161	Proposal of buried metal heterojunction bipolar transistor and fabrication of HBT with buried tungsten. , 0, , .		4
162	Vacuum microelectronic electron emitter by InP double barrier diode toward RF application. , 0, , .		0

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163	Current modulation in fine electrode by hot electron passing through GaInAs/InP double slits. , 0, , .		0
164	Fabrication and I-V characterization of metal/SAM/metal devices. , 0, , .		0
165	Freestanding tungsten wires for BM-HET. , 0, , .		1
166	InP hot electron transistor with a buried metallic gate for electron emission. , 0, , .		0
167	The impact of latent image quality on line edge roughness in electron beam lithography. , 0, , .		0
168	Improvement in Gate Insulation in InP Hot Electron Transistors for High Transconductance and High Voltage Gain. Applied Physics Express, 0, 2, 034501.	2.4	10